



PRELIMINARY AMENDMENT  
U.S. Application No. 10/591,987

Attorney Docket No.: Q80398

**AMENDMENTS TO THE SPECIFICATION**

**Please amend the first full paragraph at page 2 with the following amended paragraph:**

Conventionally, there is disclosed a technique for forming a light-emitting layer from single  $\text{Ga}_Y\text{In}_Z\text{N}$  ( $0 \leq Y$ ,  $Z \leq 1$ ,  $Y+Z=1$ ) (see JP-B SHO 55-3834). An example for forming a light-emitting layer from a super lattice structure called quantum well structure is also known (see JP-A 2001-102629). The quantum well structure is a structure in which barrier layers and well layers are alternately stacked periodically (see JP-A 2000-133883). For example, there is disclosed an embodiment in which a  $\text{Ga}_{0.7}\text{In}_{0.3}\text{N}$  layer is used as the well layer, and gallium nitride (GaN) is used as the barrier layer, and a light-emitting layer of a multiple quantum well structure is formed (see [embodiment 1] in ~~JP-A 2000-102629~~ JP-A 2001-102629).